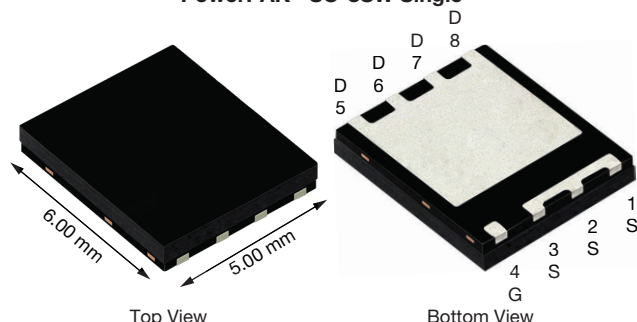


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

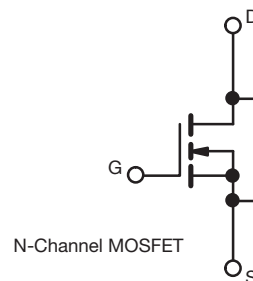
PowerPAK® SO-8SW Single



FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.00098
I_D (A) ^e	373
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK® SO-8SW
Lead (Pb)-free and halogen-free	SQRS160EP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ^e	I_D	$T_C = 25$ °C	373
		$T_C = 125$ °C	215
Continuous source current (diode conduction)	I_S	246	A
Pulsed drain current ^{a, e}	I_{DM}	778	
Single pulse avalanche current	I_{AS}	71.5	
Single pulse avalanche energy	E_{AS}	255	mJ
Maximum power dissipation ^a	P_D	$T_C = 25$ °C	270
		$T_C = 125$ °C	90
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	42	°C/W
Junction-to-case (drain) ^d	R_{thJC}	0.56	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- As per on JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.2	2.7	3.2	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.00058	0.00098	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0016	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0020	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 50 A		-	150	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	8823	12 353	pF
Output capacitance	C _{oss}			-	3284	4598	
Reverse transfer capacitance	C _{rss}			-	144	202	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 15 A	-	130	195	nC
Gate-source charge ^c	Q _{gs}			-	38	-	
Gate-drain charge ^c	Q _{gd}			-	22	-	
Gate resistance	R _g	f = 1 MHz		0.6	1.4	2.2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 2 Ω I _D ≅ 15 A, V _{GEN} = 10 V, R _g = 1 Ω		-	23	35	ns
Rise time ^c	t _r			-	14	21	
Turn-off delay time ^c	t _{d(off)}			-	53	80	
Fall time ^c	t _f			-	14	21	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	778	A
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		-	72	144	ns
Body diode reverse recovery charge	Q _{rr}			-	150	300	nC
Reverse recovery fall time	t _a			-	47	-	ns
Reverse recovery rise time	t _b			-	25	-	
Body diode peak reverse recovery current	I _{RM(REC)}					-	-3.7

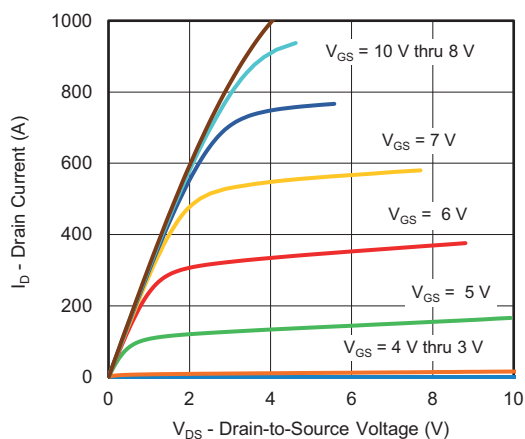
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

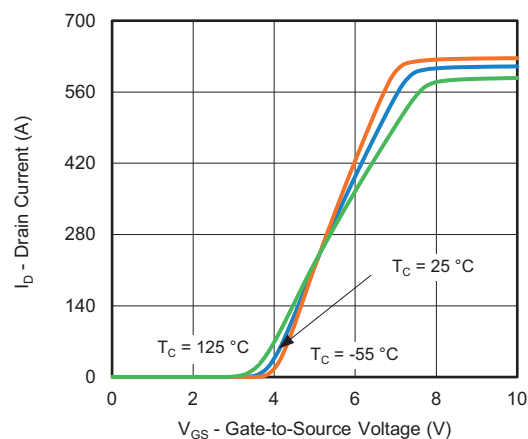
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



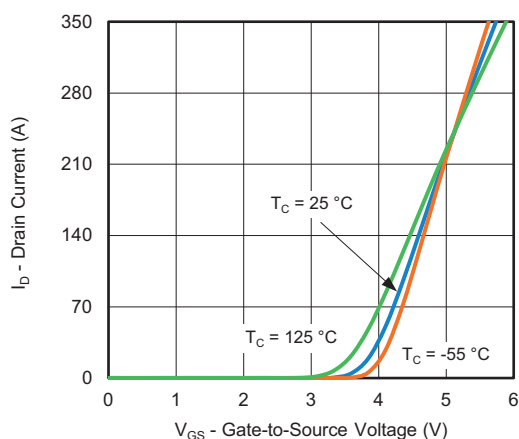
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



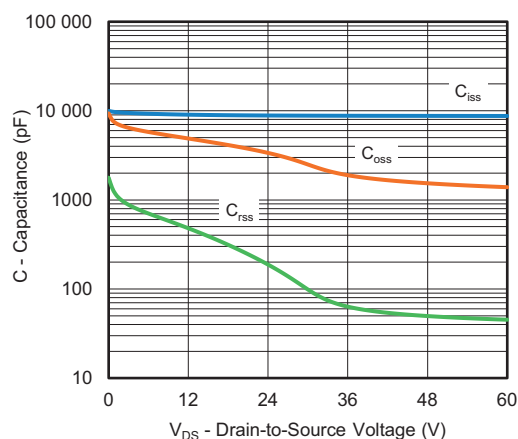
Output Characteristics



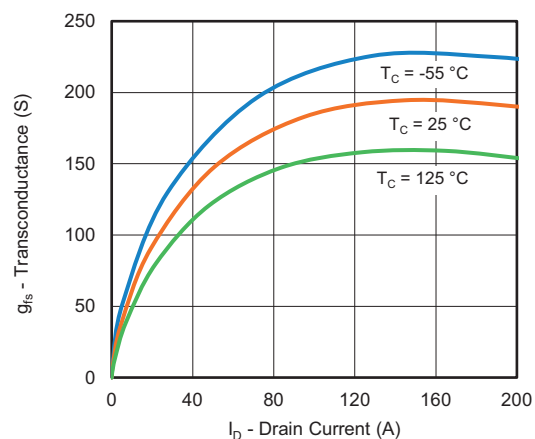
Transfer Characteristics



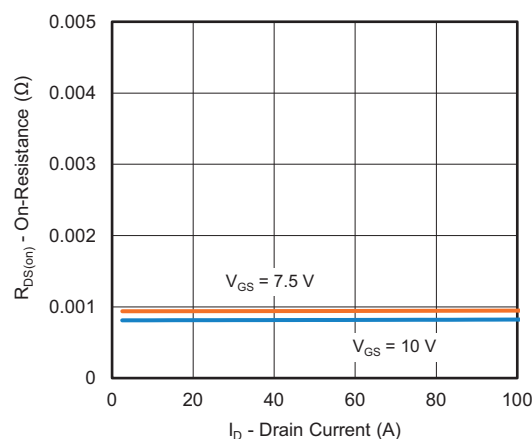
Transfer Characteristics



Capacitance



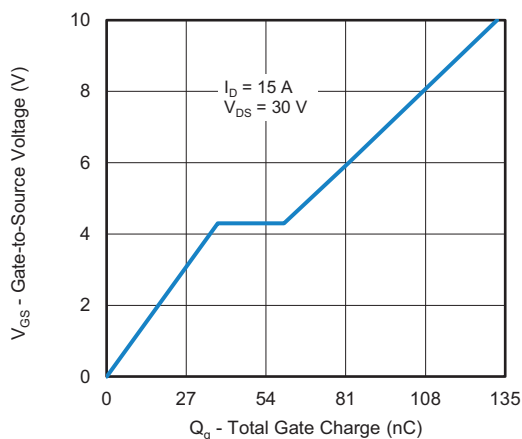
Transconductance



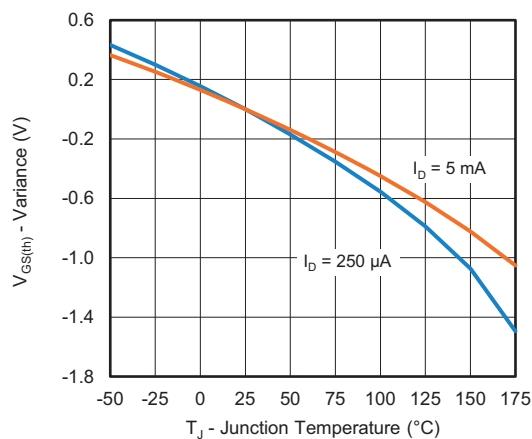
On-Resistance vs. Drain Current



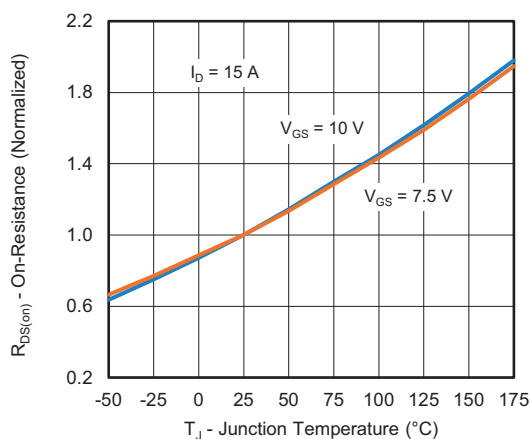
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



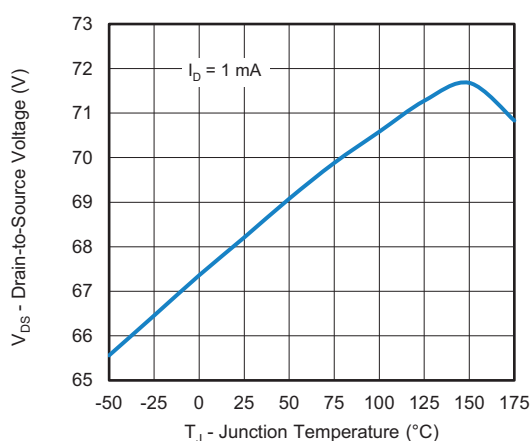
Gate Charge



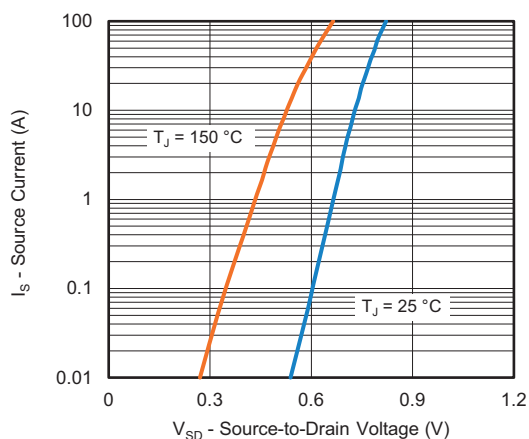
Threshold Voltage



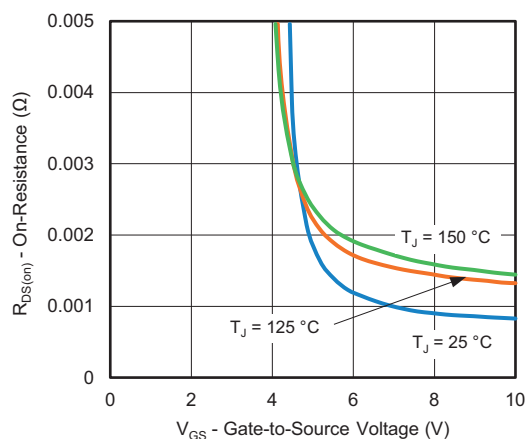
On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature



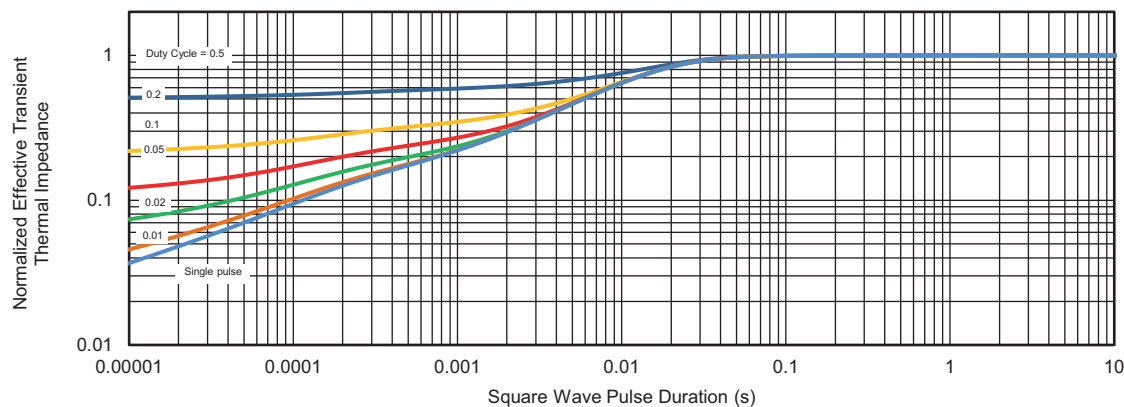
Source Drain Diode Forward Voltage



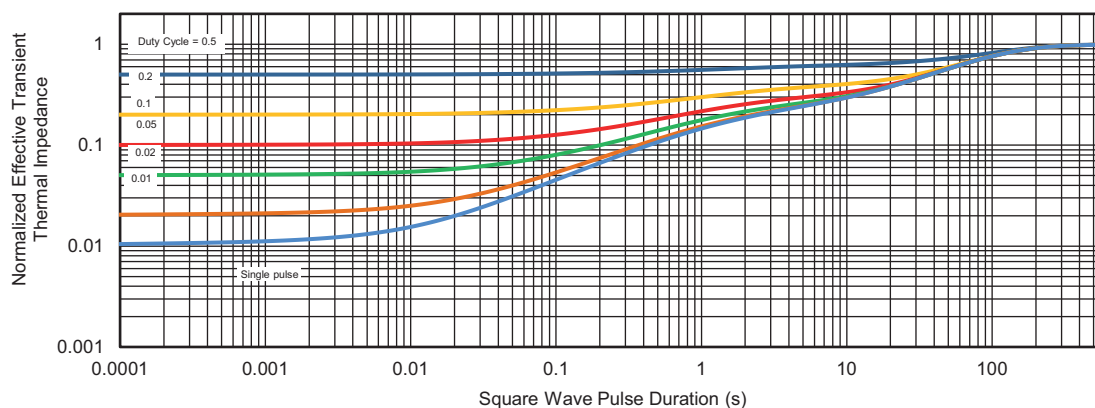
On-Resistance vs. Gate-to Source Voltage



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



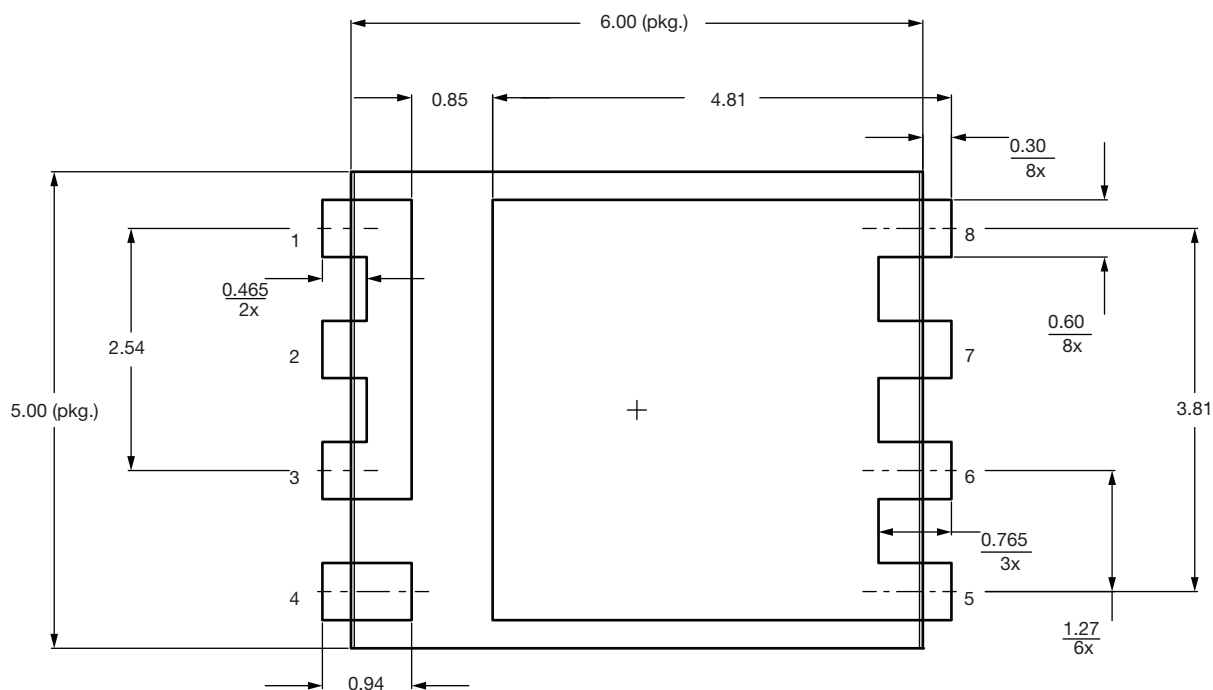
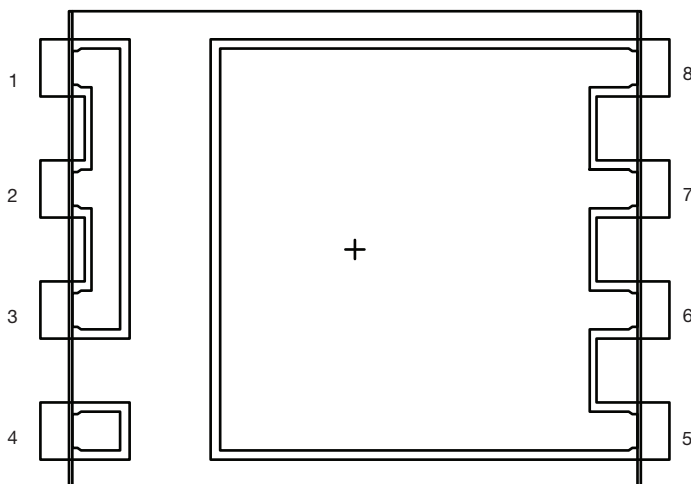
Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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Recommended Land Pattern PowerPAK® SO-8SW (PKSO8SWSCL)


Note

- Dimensions in mm

ECN: C24-0483-Rev. A, 20-May-2024
DWG: 3027



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